

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS C6

650V CoolMOS™ C6 Power Transistor  
IPx65R600C6

## Data Sheet

Rev. 2.0, 2010-08-19  
Final

Industrial & Multimarket

## 650V CoolMOS™ C6 Power Transistor

IPD65R600C6, IPI65R600C6  
IPB65R600C6, IPP65R600C6  
IPA65R600C6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

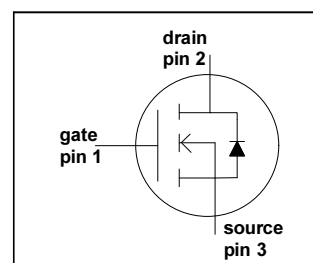
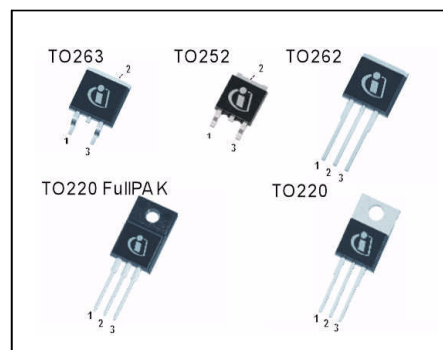
#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC<sup>1)</sup> qualified, Pb-free plating, Halogen free<sup>2)</sup>

#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*



**Table 1 Key Performance Parameters**

| Parameter            | Value | Unit       |
|----------------------|-------|------------|
| $V_{DS} @ T_{j,max}$ | 700   | V          |
| $R_{DS(on),max}$     | 0.60  | $\Omega$   |
| $Q_{g,typ}$          | 23    | nC         |
| $I_{D,pulse}$        | 18    | A          |
| $E_{oss} @ 400V$     | 2     | $\mu J$    |
| Body diode $di/dt$   | 500   | A/ $\mu s$ |

| Type / Ordering Code | Package          | Marking | Related Links                                                           |
|----------------------|------------------|---------|-------------------------------------------------------------------------|
| IPD65R600C6          | PG-TO252         | 65C6600 | <a href="#">IFX CoolMOS Webpage</a><br><a href="#">IFX Design tools</a> |
| IPI65R600C6          | PG-TO262         |         |                                                                         |
| IPB65R600C6          | PG-TO263         |         |                                                                         |
| IPP65R600C6          | PG-TO220         |         |                                                                         |
| IPA65R600C6          | PG-TO220 FullPAK |         |                                                                         |

1) J-STD20 and JESD22

2) except of PG-TO252

## Table of Contents

|   |                                           |    |
|---|-------------------------------------------|----|
| 1 | Description .....                         | 2  |
|   | Table of Contents .....                   | 3  |
| 2 | Maximum ratings .....                     | 4  |
| 3 | Thermal characteristics .....             | 5  |
| 4 | Electrical characteristics .....          | 6  |
| 5 | Electrical characteristics diagrams ..... | 8  |
| 6 | Test circuits .....                       | 13 |
| 7 | Package outlines .....                    | 14 |
| 8 | Revision History .....                    | 19 |

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

| Parameter                                            | Symbol         | Values |      |      | Unit | Note / Test Condition                                                      |
|------------------------------------------------------|----------------|--------|------|------|------|----------------------------------------------------------------------------|
|                                                      |                | Min.   | Typ. | Max. |      |                                                                            |
| Continuous drain current <sup>1)</sup>               | $I_D$          | -      | -    | 7.3  | A    | $T_C = 25\text{ °C}$                                                       |
|                                                      |                |        |      | 4.6  |      | $T_C = 100\text{ °C}$                                                      |
| Pulsed drain current <sup>2)</sup>                   | $I_{D,pulse}$  | -      | -    | 18   | A    | $T_C = 25\text{ °C}$                                                       |
| Avalanche energy, single pulse                       | $E_{AS}$       | -      | -    | 142  | mJ   | $I_D = 1.3\text{ A}, V_{DD} = 50\text{ V}$<br>(see table 21)               |
| Avalanche energy, repetitive                         | $E_{AR}$       | -      | -    | 0.21 |      | $I_D = 1.3\text{ A}, V_{DD} = 50\text{ V}$                                 |
| Avalanche current, repetitive                        | $I_{AR}$       | -      | -    | 1.3  | A    |                                                                            |
| MOSFET dv/dt ruggedness                              | dv/dt          | -      | -    | 50   | V/ns | $V_{DS} = 0 \dots 480\text{ V}$                                            |
| Gate source voltage                                  | $V_{GS}$       | -20    | -    | 20   | V    | static                                                                     |
|                                                      |                | -30    |      | 30   |      | AC ( $f > 1\text{ Hz}$ )                                                   |
| Power dissipation for TO-220, TO-252, TO-262, TO-263 | $P_{tot}$      | -      | -    | 63   | W    | $T_C = 25\text{ °C}$                                                       |
| Power dissipation for TO-220 FullPAK                 | $P_{tot}$      | -      | -    | 28   | W    | $T_C = 25\text{ °C}$                                                       |
| Operating and storage temperature                    | $T_j, T_{stg}$ | -55    | -    | 150  | °C   |                                                                            |
| Mounting torque TO-220                               |                | -      | -    | 60   | Ncm  | M3 and M3.5 screws                                                         |
| Mounting torque TO-220 FullPAK                       |                |        |      | 50   |      | M2.5 screws                                                                |
| Continuous diode forward current                     | $I_S$          | -      | -    | 6.3  | A    | $T_C = 25\text{ °C}$                                                       |
| Diode pulse current <sup>2)</sup>                    | $I_{S,pulse}$  | -      | -    | 18   | A    | $T_C = 25\text{ °C}$                                                       |
| Reverse diode dv/dt <sup>3)</sup>                    | dv/dt          | -      | -    | 15   | V/ns | $V_{DS} = 0 \dots 480\text{ V}, I_{SD} \leq I_D,$<br>$T_j = 125\text{ °C}$ |
| Maximum diode commutation speed <sup>3)</sup>        | di/dt          |        |      | 500  | A/μs | (see table 22)                                                             |

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220 & TO-262**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition                 |
|------------------------------------------------------------|------------|--------|------|------|------|---------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                       |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 2.0  | °C/W |                                       |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 62   |      | lead                                  |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6 mm (0.063 in.) from case for 10 s |

**Table 4 Thermal characteristics TO-220FullPAK**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition                 |
|------------------------------------------------------------|------------|--------|------|------|------|---------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                       |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 4.5  | °C/W |                                       |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 80   |      | lead                                  |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6 mm (0.063 in.) from case for 10 s |

**Table 5 Thermal characteristics TO-263 & TO-252**

| Parameter                                              | Symbol     | Values |      |      | Unit | Note / Test Condition                                                   |
|--------------------------------------------------------|------------|--------|------|------|------|-------------------------------------------------------------------------|
|                                                        |            | Min.   | Typ. | Max. |      |                                                                         |
| Thermal resistance, junction - case                    | $R_{thJC}$ | -      | -    | 2.0  | °C/W |                                                                         |
| Thermal resistance, junction - ambient                 | $R_{thJA}$ | -      | -    | 62   |      | SMD version, device on PCB, minimal footprint                           |
|                                                        |            |        | 35   |      |      | SMD version, device on PCB, 6cm <sup>2</sup> cooling area <sup>1)</sup> |
| Soldering temperature, wave- & reflowsoldering allowed | $T_{sold}$ | -      | -    | 260  | °C   | reflow MSL1                                                             |

1) Device on 40mm\*40mm\*1.5 epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70µm thick) copper area for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 6 Static characteristics**

| Parameter                        | Symbol        | Values |      |      | Unit          | Note / Test Condition                                                |
|----------------------------------|---------------|--------|------|------|---------------|----------------------------------------------------------------------|
|                                  |               | Min.   | Typ. | Max. |               |                                                                      |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 650    | -    | -    | V             | $V_{GS}=0\text{ V}$ , $I_D=1.0\text{ mA}$                            |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.5    | 3    | 3.5  |               | $V_{DS}=V_{GS}$ , $I_D=0.21\text{ mA}$                               |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | -    | 1    | $\mu\text{A}$ | $V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$  |
|                                  |               | -      | 10   | -    |               | $V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=150\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | -    | 100  | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                           |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 0.54 | 0.6  | $\Omega$      | $V_{GS}=10\text{ V}$ , $I_D=2.1\text{ A}$ ,<br>$T_j=25\text{ °C}$    |
|                                  |               | -      | 1.40 | -    |               | $V_{GS}=10\text{ V}$ , $I_D=2.1\text{ A}$ ,<br>$T_j=150\text{ °C}$   |
| Gate resistance                  | $R_G$         | -      | 17.5 | -    | $\Omega$      | $f=1\text{ MHz}$ , open drain                                        |

**Table 7 Dynamic characteristics**

| Parameter                                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                                                               |
|------------------------------------------------------------|--------------|--------|------|------|------|---------------------------------------------------------------------------------------------------------------------|
|                                                            |              | Min.   | Typ. | Max. |      |                                                                                                                     |
| Input capacitance                                          | $C_{iss}$    | -      | 440  | -    | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ ,<br>$f=1\text{ MHz}$                                                   |
| Output capacitance                                         | $C_{oss}$    | -      | 30   | -    |      |                                                                                                                     |
| Effective output capacitance, energy related <sup>1)</sup> | $C_{o(er)}$  | -      | 21   | -    |      | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=0\dots480\text{ V}$                                                                |
| Effective output capacitance, time related <sup>2)</sup>   | $C_{o(tr)}$  | -      | 88   | -    |      | $I_D=\text{constant}$ , $V_{GS}=0\text{ V}$<br>$V_{DS}=0\dots480\text{ V}$                                          |
| Turn-on delay time                                         | $t_{d(on)}$  | -      | 12   | -    | ns   | $V_{DD}=400\text{ V}$ ,<br>$V_{GS}=13\text{ V}$ , $I_D=3.2\text{ A}$ ,<br>$R_G=6.8\text{ }\Omega$<br>(see table 20) |
| Rise time                                                  | $t_r$        | -      | 9    | -    |      |                                                                                                                     |
| Turn-off delay time                                        | $t_{d(off)}$ | -      | 80   | -    |      |                                                                                                                     |
| Fall time                                                  | $t_f$        | -      | 13   | -    |      |                                                                                                                     |

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 8 Gate charge characteristics**

| Parameter              | Symbol        | Values |      |      | Unit | Note / Test Condition                                                            |
|------------------------|---------------|--------|------|------|------|----------------------------------------------------------------------------------|
|                        |               | Min.   | Typ. | Max. |      |                                                                                  |
| IGate to source charge | $Q_{gs}$      | -      | 2.75 | -    | nC   | $V_{DD}=480\text{ V}$ , $I_D=3.2\text{ A}$ ,<br>$V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge   | $Q_{gd}$      | -      | 12   | -    |      |                                                                                  |
| Gate charge total      | $Q_g$         | -      | 23   | -    |      |                                                                                  |
| Gate plateau voltage   | $V_{plateau}$ | -      | 5.5  | -    | V    |                                                                                  |

**Table 9 Reverse diode characteristics**

| Parameter                     | Symbol    | Values |      |      | Unit          | Note / Test Condition                                                                             |
|-------------------------------|-----------|--------|------|------|---------------|---------------------------------------------------------------------------------------------------|
|                               |           | Min.   | Typ. | Max. |               |                                                                                                   |
| Diode forward voltage         | $V_{SD}$  | -      | 0.9  | -    | V             | $V_{GS}=0\text{ V}$ , $I_F=3.2\text{ A}$ ,<br>$T_j=25\text{ °C}$                                  |
| Reverse recovery time         | $t_{rr}$  | -      | 270  | -    | ns            | $V_R=400\text{ V}$ , $I_F=3.2\text{ A}$ ,<br>$di_F/dt=100\text{ A}/\mu\text{s}$<br>(see table 22) |
| Reverse recovery charge       | $Q_{rr}$  | -      | 2    | -    | $\mu\text{C}$ |                                                                                                   |
| Peak reverse recovery current | $I_{rrm}$ | -      | 13   | -    | A             |                                                                                                   |

## 5 Electrical characteristics diagrams

Table 10

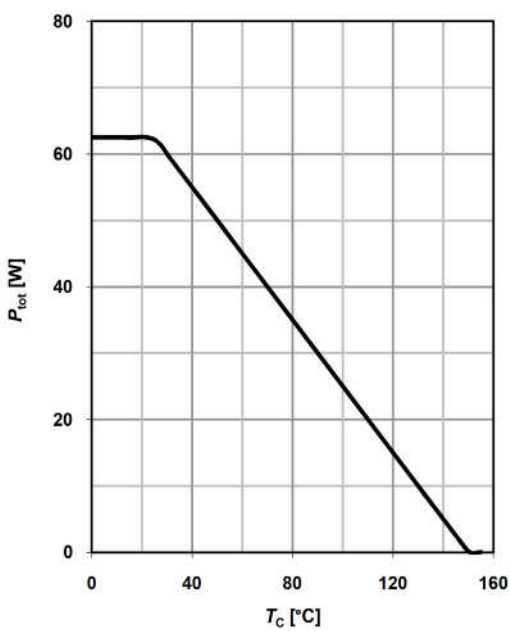
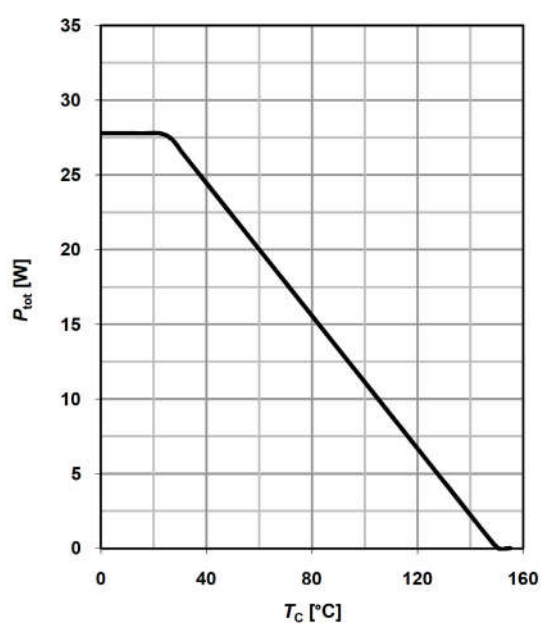
| Power dissipation<br>Non FullPAK                                                   | Power dissipation<br>FullPAK                                                        |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $P_{tot} = f(T_c)$                                                                 | $P_{tot} = f(T_c)$                                                                  |

Table 11

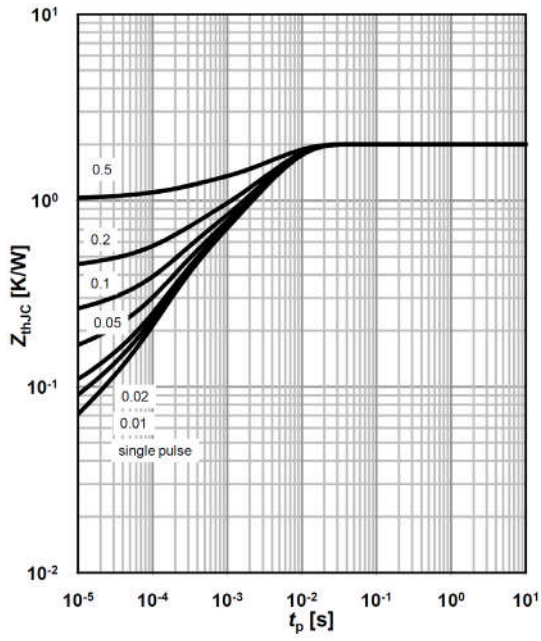
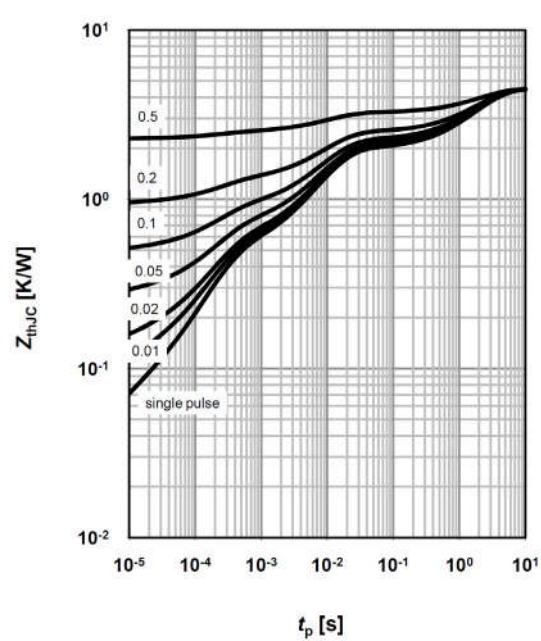
| Max. transient thermal impedance<br>Non FullPAK                                     | Max. transient thermal impedance<br>FullPAK                                          |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p / T$                                    | $Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p / T$                                     |

Table 12

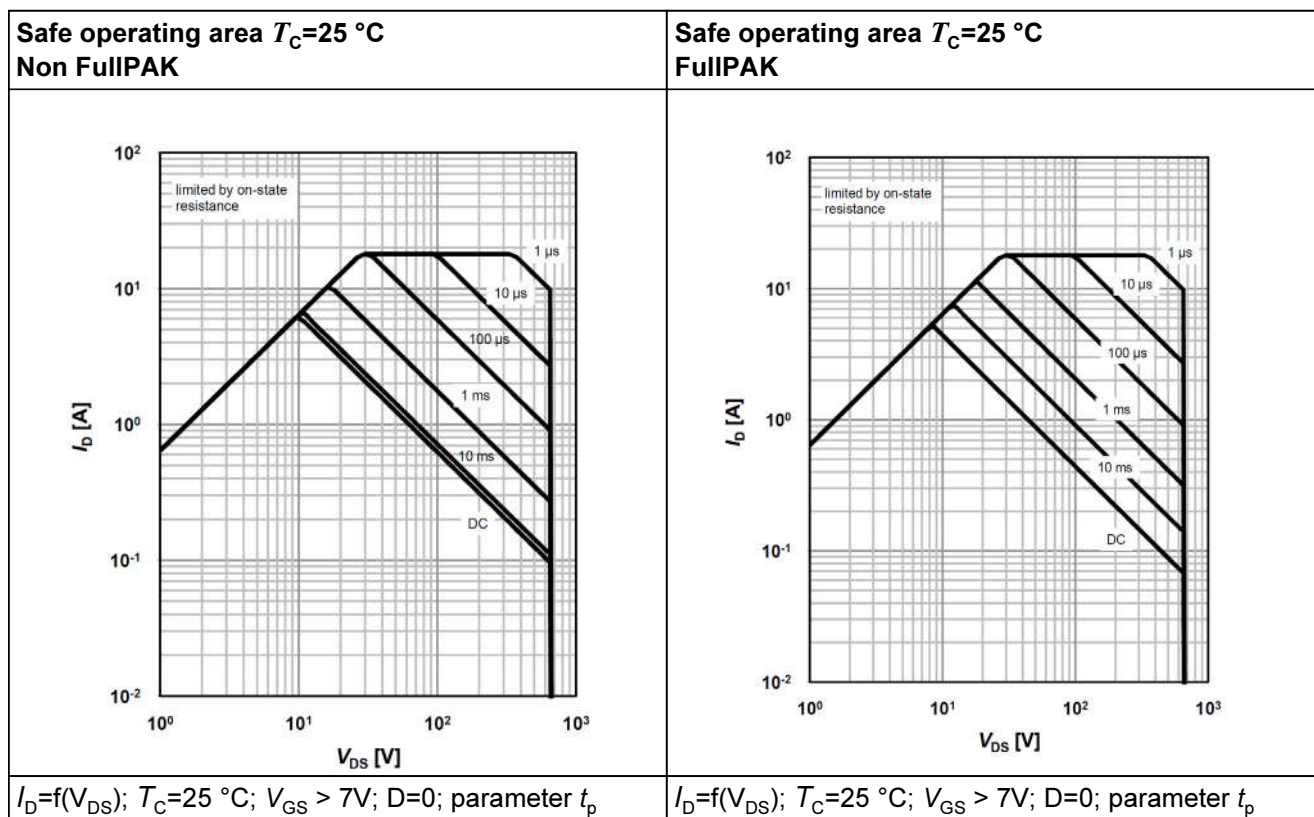
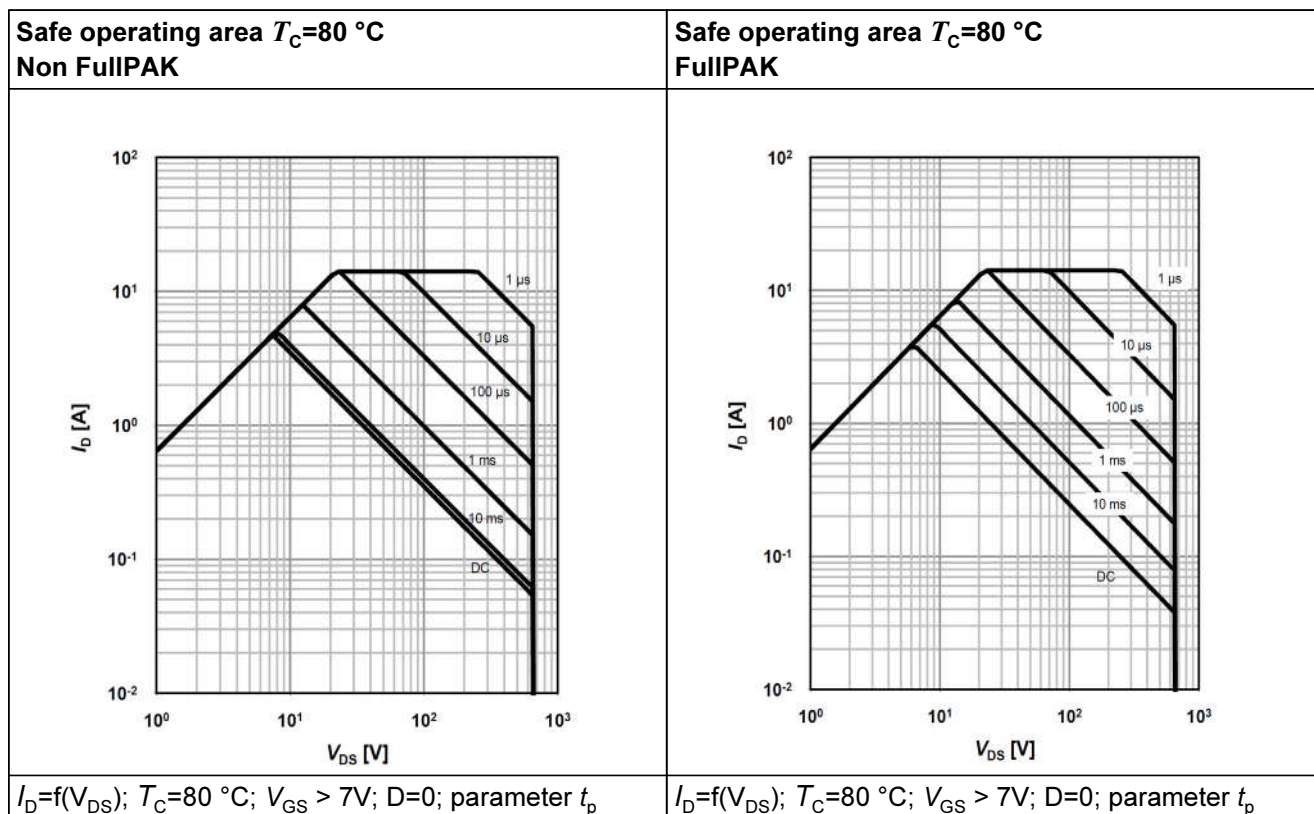


Table 13



Electrical characteristics diagrams

Table 14

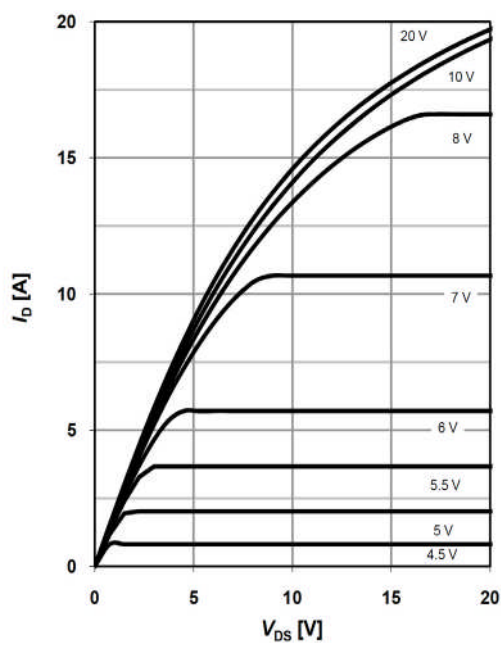
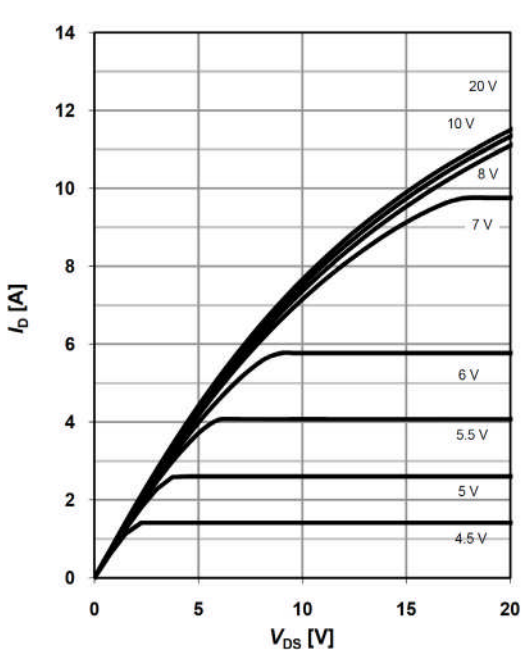
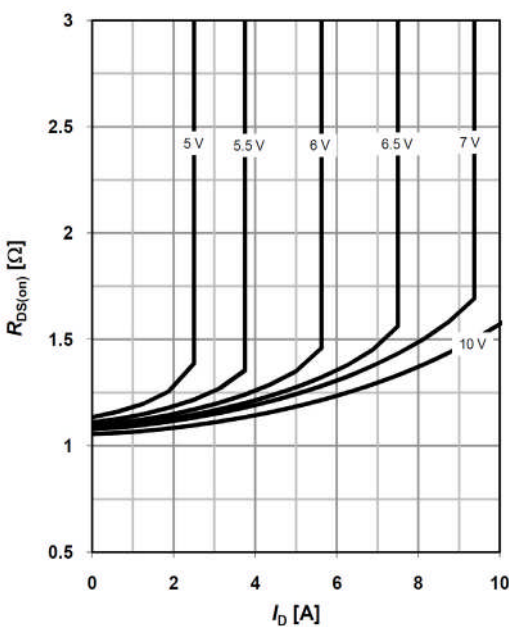
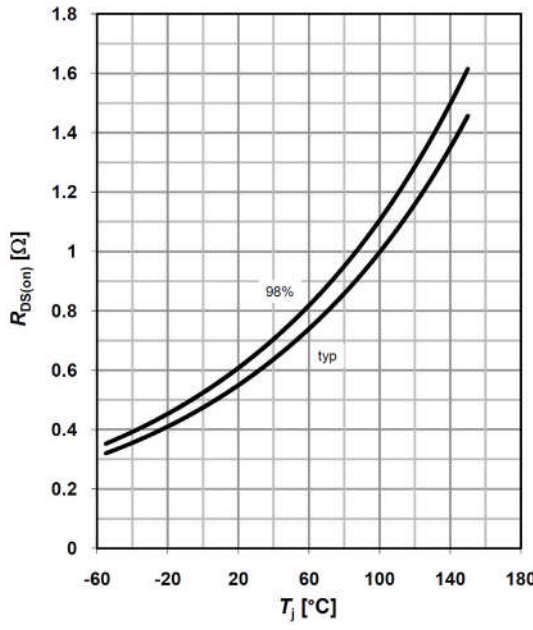
| Typ. output characteristics $T_j=25\text{ °C}$                                     | Typ. output characteristics $T_j=125\text{ °C}$                                     |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $I_D=f(V_{DS}); T_j=25\text{ °C}; \text{parameter: } V_{GS}$                       | $I_D=f(V_{DS}); T_j=125\text{ °C}; \text{parameter: } V_{GS}$                       |

Table 15

| Typ. drain-source on-state resistance                                               | Drain-source on-state resistance                                                     |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $R_{DS(on)}=f(I_D); T_j=125\text{ °C}; \text{parameter: } V_{GS}$                   | $R_{DS(on)}=f(T_j); I_D=3.2\text{ A}; V_{GS}=10\text{ V}$                            |

Electrical characteristics diagrams

Table 16

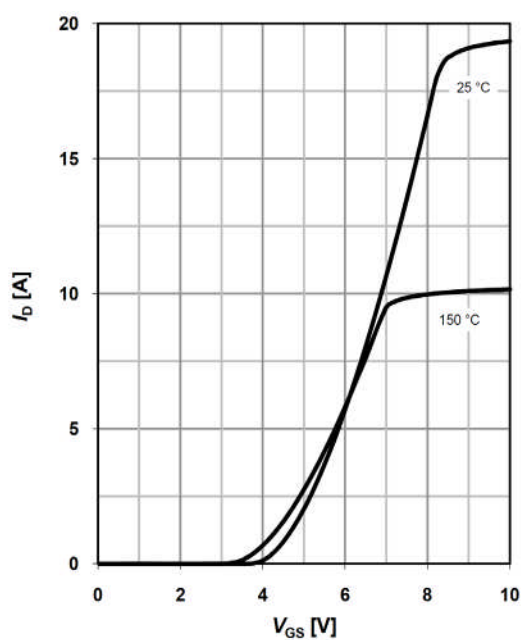
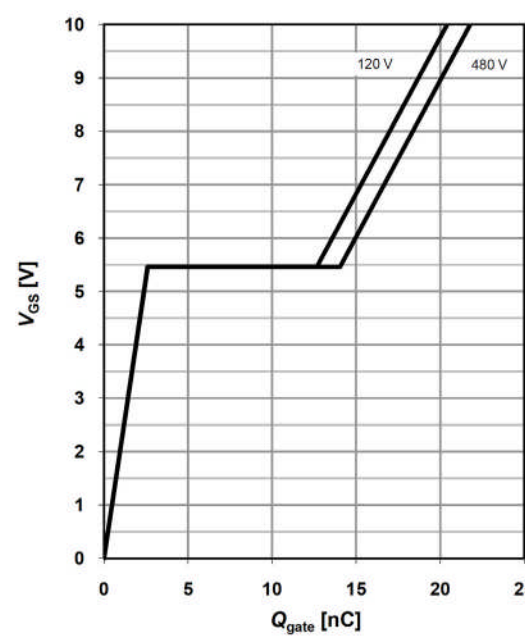
| Typ. transfer characteristics                                                      | Typ. gate charge                                                                    |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $I_D = f(V_{GS}); V_{DS} = 20V$                                                    | $V_{GS} = f(Q_{gate}), I_D = 2.1 \text{ A pulsed}$                                  |

Table 17

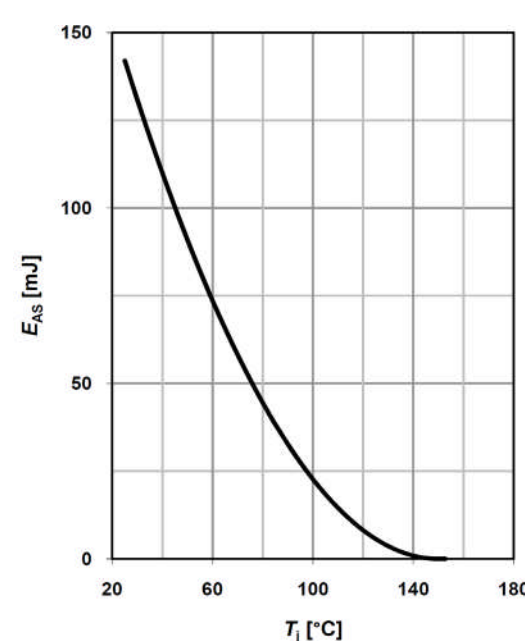
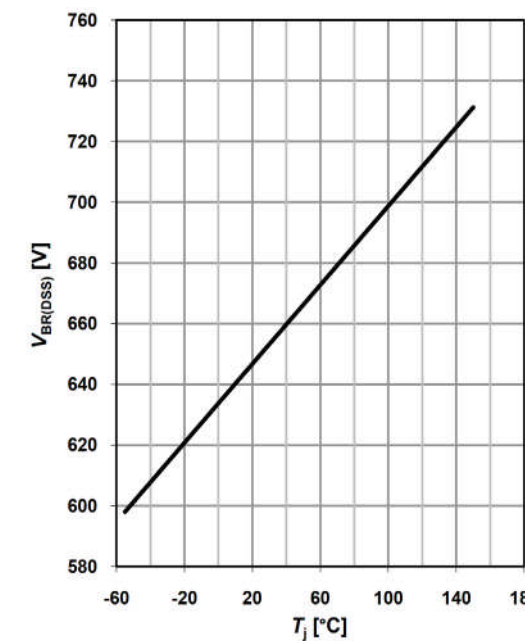
| Avalanche energy                                                                    | Drain-source breakdown voltage                                                       |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $E_{AS} = f(T_j); I_D = 1.8 \text{ A}; V_{DD} = 50 \text{ V}$                       | $V_{BR(DSS)} = f(T_j); I_D = 1.0 \text{ mA}$                                         |

Table 18

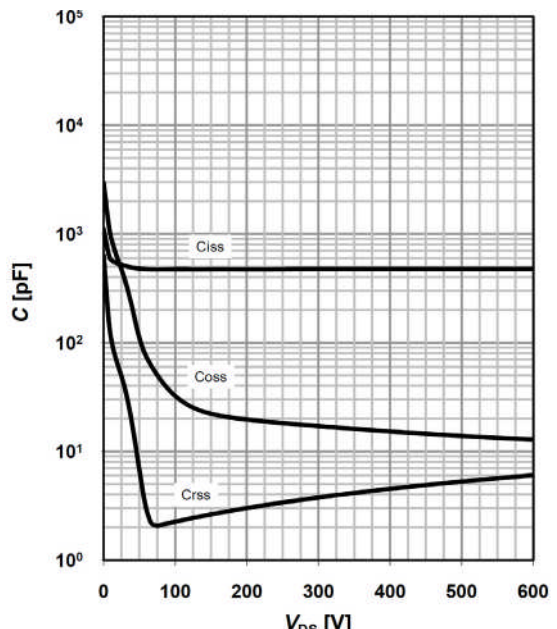
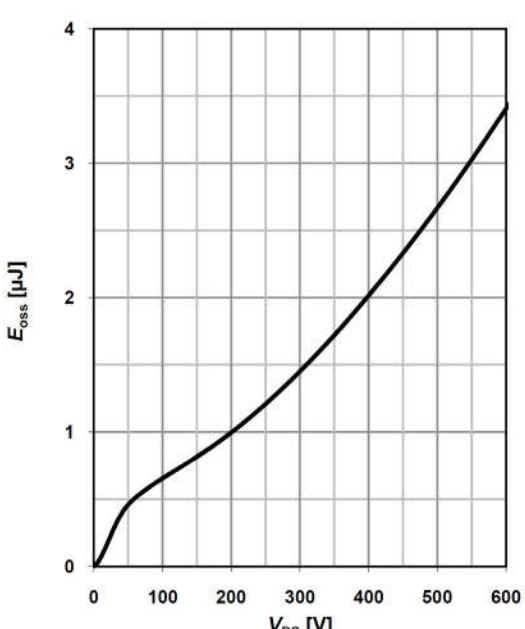
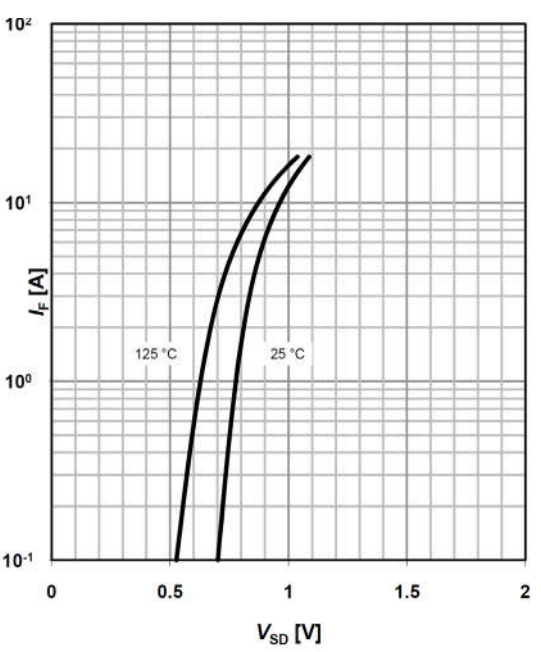
| Typ. capacitances                                                                  | Typ. $C_{oss}$ stored energy                                                        |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$                                   | $E_{oss}=f(V_{DS})$                                                                 |

Table 19

| Forward characteristics of reverse diode                                            |
|-------------------------------------------------------------------------------------|
|  |
| $I_F=f(V_{SD}); \text{parameter: } T_j$                                             |

## 6 Test circuits

Table 20 Switching times test circuit and waveform for inductive load

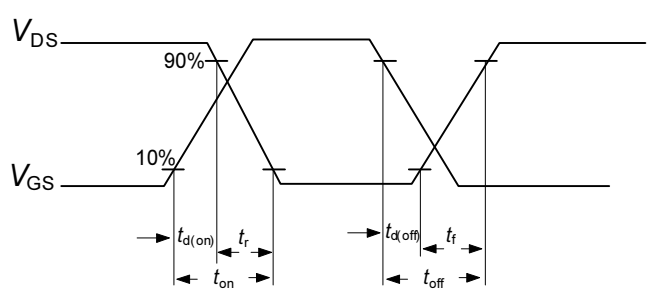
| Switching times test circuit for inductive load                                   | Switching time waveform                                                            |
|-----------------------------------------------------------------------------------|------------------------------------------------------------------------------------|
|  |  |

Table 21 Unclamped inductive load test circuit and waveform

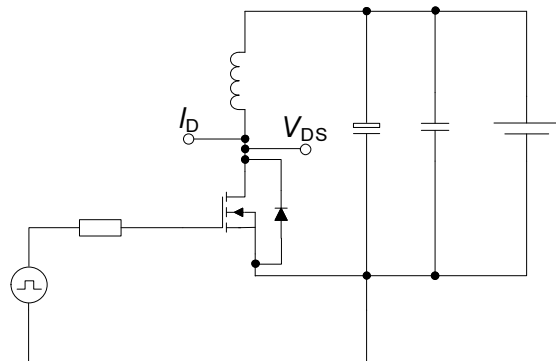
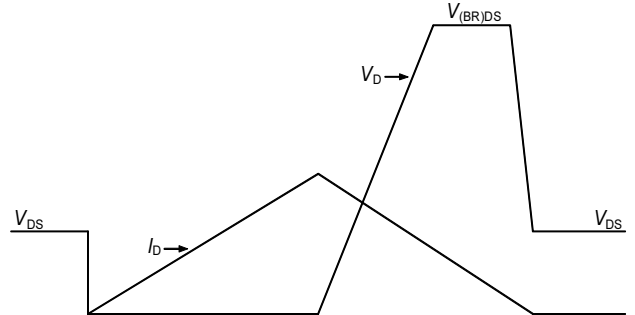
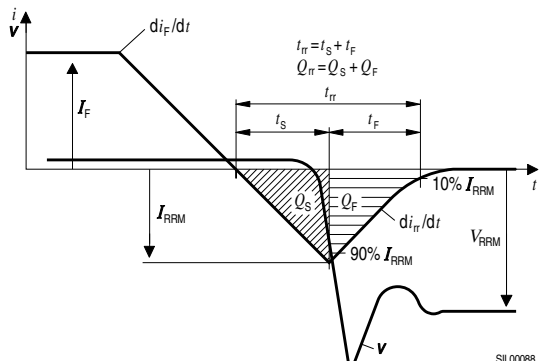
| Unclamped inductive load test circuit                                               | Unclamped inductive waveform                                                         |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |

Table 22 Test circuit and waveform for diode characteristics

| Test circuit for diode characteristics                                                                                  | Diode recovery waveform                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                        |
|-------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>R_{G1} = R_{G2}</math></p> |  <p><math>i</math><br/><math>v</math><br/><math>I_F</math><br/><math>I_{RRM}</math><br/><math>t_{rr}</math><br/><math>t_s</math><br/><math>t_F</math><br/><math>Q_{rr} = Q_S + Q_F</math><br/><math>Q_S</math><br/><math>Q_F</math><br/><math>10\% I_{RRM}</math><br/><math>90\% I_{RRM}</math><br/><math>V_{RRM}</math><br/><math>d i_F / d t</math><br/><math>d i_{rr} / d t</math><br/><math>t_{rr} = t_s + t_F</math><br/>SIL00088</p> |

## 7 Package outlines

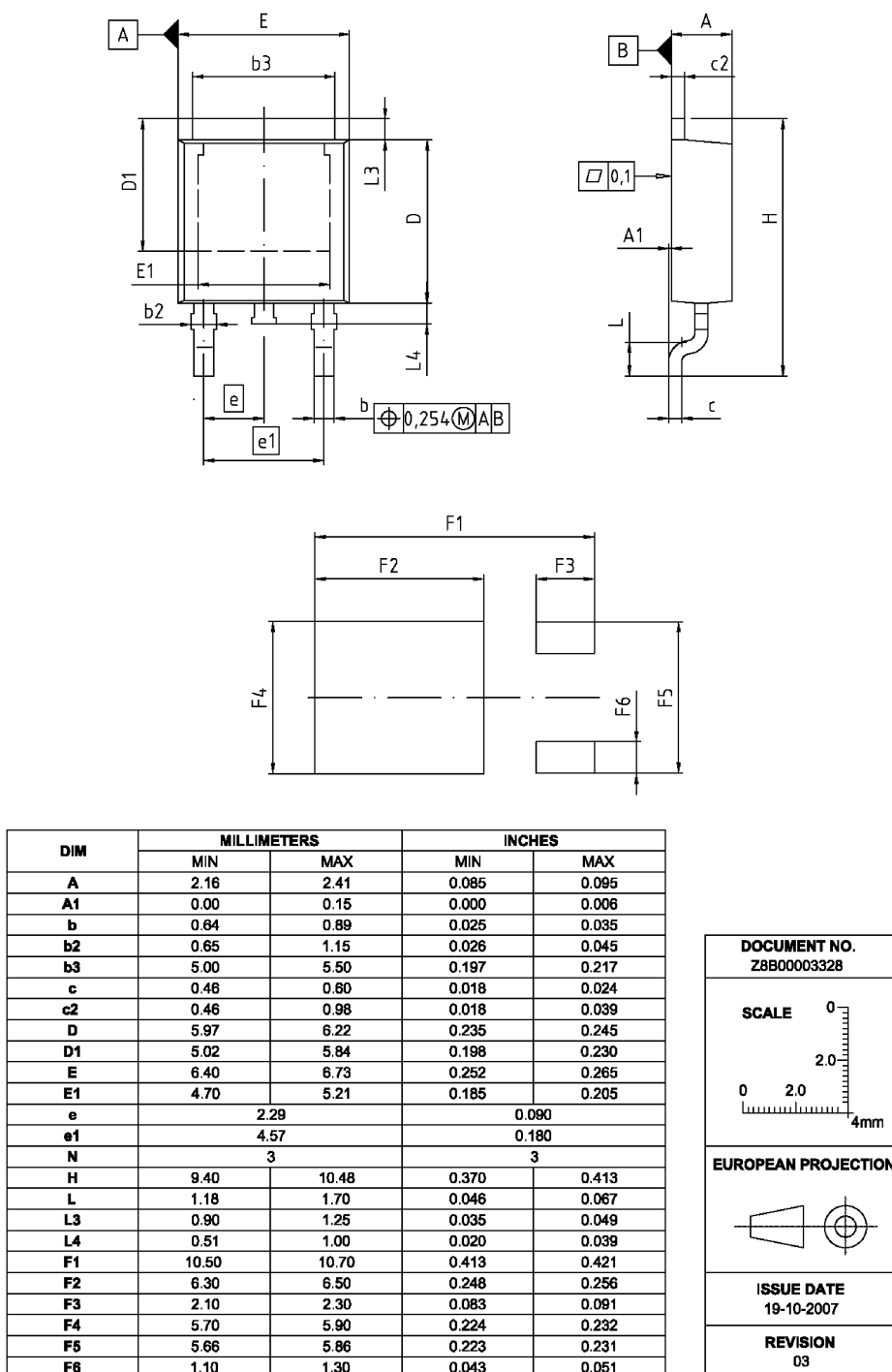
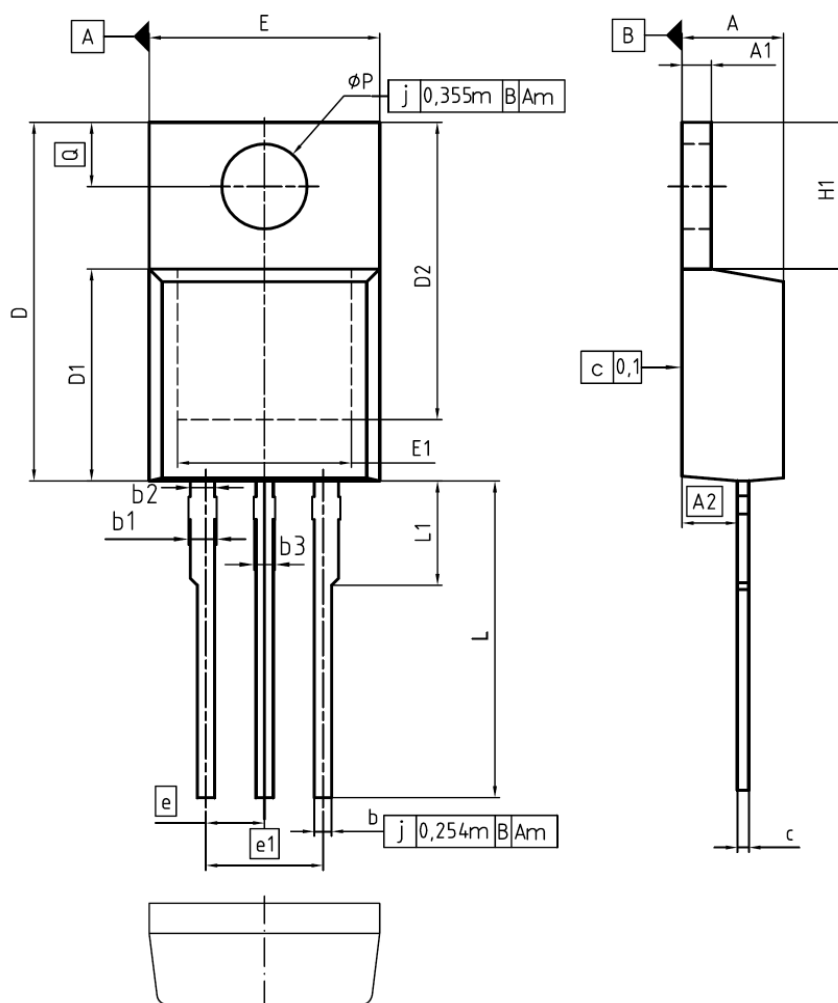
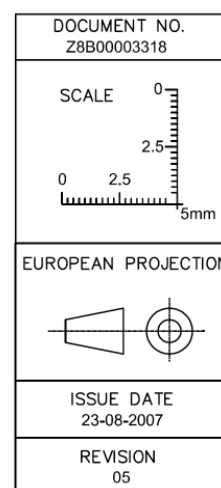


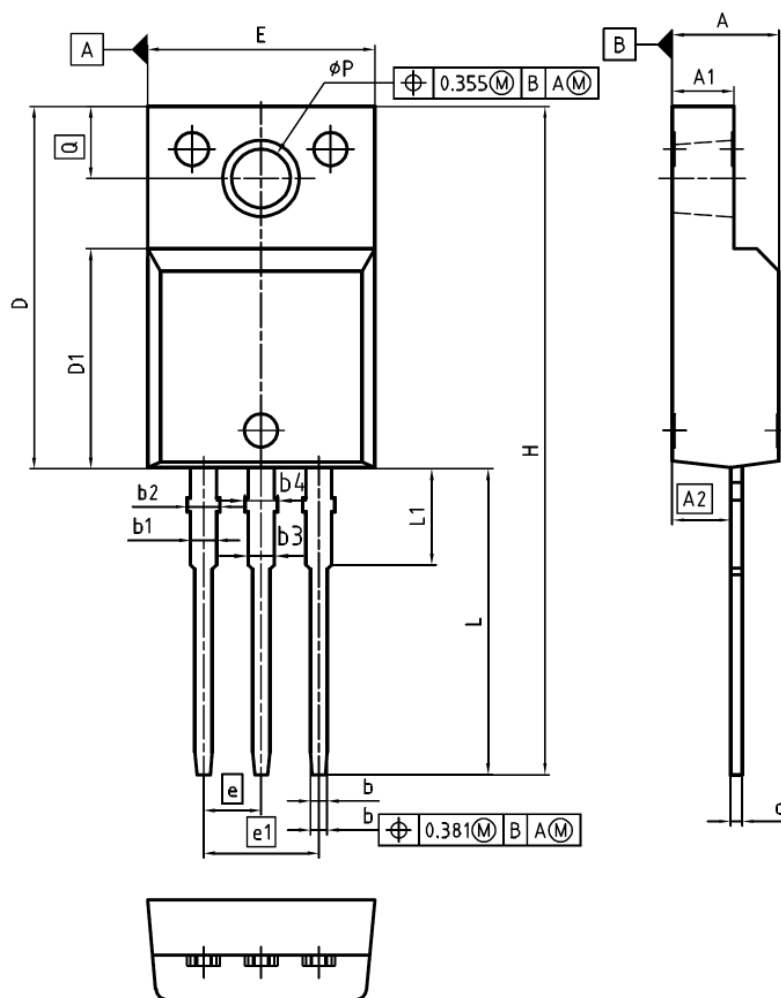
Figure 1 Outlines TO-252, dimensions in mm/inches



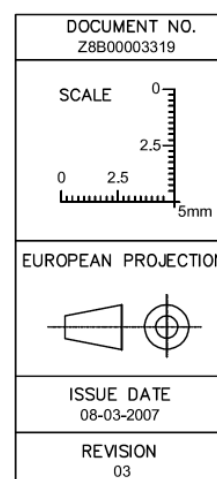
| DIM   | MILLIMETERS |       | INCHES |       |
|-------|-------------|-------|--------|-------|
|       | MIN         | MAX   | MIN    | MAX   |
| A     | 4.30        | 4.57  | 0.169  | 0.180 |
| A1    | 1.17        | 1.40  | 0.046  | 0.055 |
| A2    | 2.15        | 2.72  | 0.085  | 0.107 |
| b     | 0.65        | 0.86  | 0.026  | 0.034 |
| b1    | 0.95        | 1.40  | 0.037  | 0.055 |
| b2    | 0.95        | 1.15  | 0.037  | 0.045 |
| b3    | 0.65        | 1.15  | 0.026  | 0.045 |
| c     | 0.33        | 0.60  | 0.013  | 0.024 |
| D     | 14.81       | 15.95 | 0.583  | 0.628 |
| D1    | 8.51        | 9.45  | 0.335  | 0.372 |
| D2    | 12.19       | 13.10 | 0.480  | 0.516 |
| E     | 9.70        | 10.36 | 0.382  | 0.408 |
| E1    | 6.50        | 8.60  | 0.256  | 0.339 |
| e     | 2.54        |       | 0.100  |       |
| e1    | 5.08        |       | 0.200  |       |
| N     | 3           |       | 3      |       |
| H1    | 5.90        | 6.90  | 0.232  | 0.272 |
| L     | 13.00       | 14.00 | 0.512  | 0.551 |
| L1    | -           | 4.80  | -      | 0.189 |
| phi P | 3.60        | 3.89  | 0.142  | 0.153 |
| Q     | 2.60        | 3.00  | 0.102  | 0.118 |



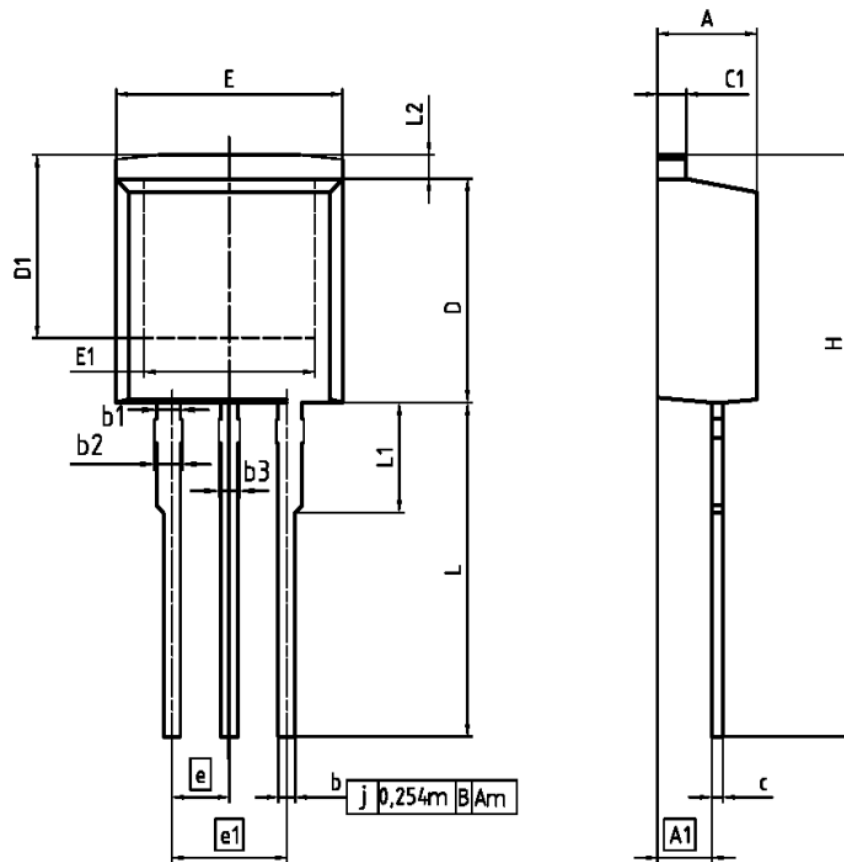
**Figure 2** Outlines TO-220, dimensions in mm/inches



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.55        | 4.85  | 0.179  | 0.191 |
| A1  | 2.55        | 2.85  | 0.100  | 0.112 |
| A2  | 2.42        | 2.72  | 0.095  | 0.107 |
| b   | 0.65        | 0.85  | 0.026  | 0.033 |
| b1  | 0.95        | 1.33  | 0.037  | 0.052 |
| b2  | 0.95        | 1.51  | 0.037  | 0.059 |
| b3  | 0.65        | 1.33  | 0.026  | 0.052 |
| b4  | 0.65        | 1.51  | 0.026  | 0.059 |
| c   | 0.40        | 0.63  | 0.016  | 0.025 |
| D   | 15.85       | 16.15 | 0.624  | 0.636 |
| D1  | 9.53        | 9.83  | 0.375  | 0.387 |
| E   | 10.35       | 10.65 | 0.407  | 0.419 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H   | 29.45       | 29.75 | 1.159  | 1.171 |
| L   | 13.45       | 13.75 | 0.530  | 0.541 |
| L1  | 3.15        | 3.45  | 0.124  | 0.136 |
| ØP  | 2.95        | 3.20  | 0.116  | 0.126 |
| Q   | 3.15        | 3.50  | 0.124  | 0.138 |



**Figure 3** Outlines TO-220 FullPAK, dimensions in mm/inches



| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 4.300       | 4.572  | 0.169  | 0.180 |
| A1  | 2.150       | 2.718  | 0.085  | 0.107 |
| b   | 0.650       | 0.864  | 0.026  | 0.034 |
| b1  | 0.950       | 1.093  | 0.037  | 0.043 |
| b2  | 0.950       | 1.400  | 0.037  | 0.055 |
| b3  | 0.650       | 1.118  | 0.026  | 0.044 |
| c   | 0.330       | 0.600  | 0.013  | 0.024 |
| c1  | 1.170       | 1.400  | 0.046  | 0.055 |
| D   | 8.509       | 8.450  | 0.335  | 0.372 |
| D1  | 6.900       | -      | 0.272  | -     |
| E   | 9.700       | 10.363 | 0.382  | 0.408 |
| E1  | 6.500       | 8.600  | 0.256  | 0.339 |
| e   | 2.540       |        | 0.100  |       |
| e1  | 5.080       |        | 0.200  |       |
| N   | 3           |        | 3      |       |
| L   | 13.000      | 14.000 | 0.512  | 0.551 |
| L1  | -           | 4.800  | -      | 0.189 |
| L2  | -           | 1.727  | -      | 0.068 |

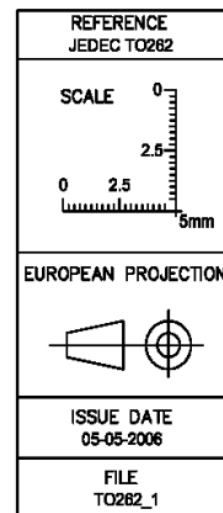
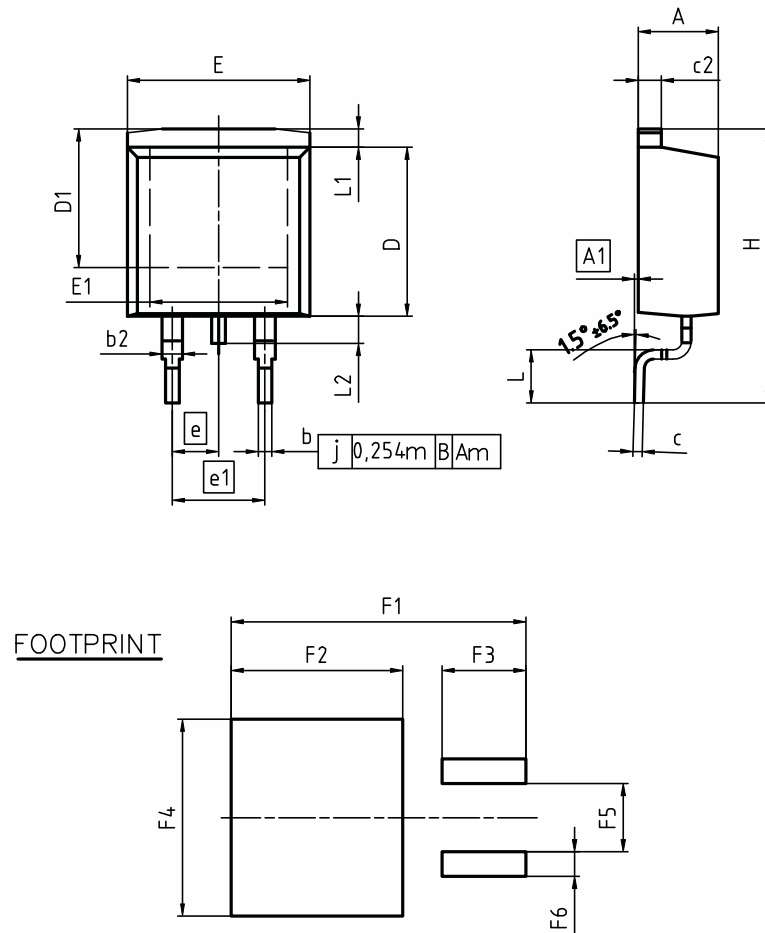
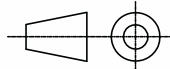


Figure 4 Outlines TO-262, dimensions in mm/inches



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 0.00        | 0.25  | 0.000  | 0.010 |
| b   | 0.65        | 0.85  | 0.026  | 0.033 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| c   | 0.33        | 0.65  | 0.013  | 0.026 |
| c2  | 1.17        | 1.40  | 0.046  | 0.055 |
| D   | 8.51        | 9.45  | 0.335  | 0.372 |
| D1  | 7.10        | 7.90  | 0.280  | 0.311 |
| E   | 9.80        | 10.31 | 0.386  | 0.406 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 2           |       | 2      |       |
| H   | 14.61       | 15.88 | 0.575  | 0.625 |
| L   | 2.29        | 3.00  | 0.090  | 0.118 |
| L1  | 0.70        | 1.60  | 0.028  | 0.063 |
| L2  | 1.00        | 1.78  | 0.039  | 0.070 |
| F1  | 16.05       | 16.25 | 0.632  | 0.640 |
| F2  | 9.30        | 9.50  | 0.366  | 0.374 |
| F3  | 4.50        | 4.70  | 0.177  | 0.185 |
| F4  | 10.70       | 10.90 | 0.421  | 0.429 |
| F5  | 3.65        | 3.85  | 0.144  | 0.152 |
| F6  | 1.25        | 1.45  | 0.049  | 0.057 |

|                                                                                                              |
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| ISSUE DATE<br><b>30-08-2007</b>                                                                              |
| REVISION<br><b>01</b>                                                                                        |

**Figure5 Outlines TO-263, dimensions in mm/inches**

## 8 Revision History

Revision History: 2010-08-19, Rev. 2.0

Previous Revision:

| Revision | Subjects (major changes since last revision) |
|----------|----------------------------------------------|
| 2.0      | Release of final data sheet                  |
|          |                                              |
|          |                                              |

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